

SiW-ECAL Status and Prospectives

Vincent Boudry



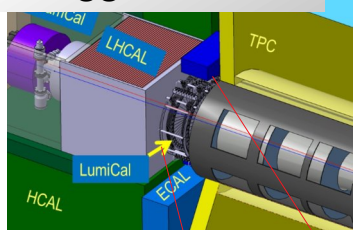
Institut Polytechnique de Paris

CEPC EU WS 2025, Barcelona, 17/05/2025

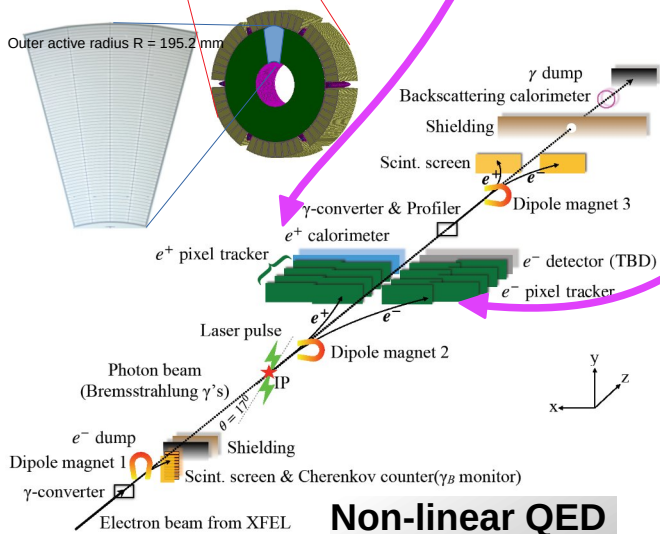
A Map to High-Granularity Calorimeter Prototypes

FCAL for ILD, LUXE

For Higgs Factories



Outer active radius $R = 195.2$ mm

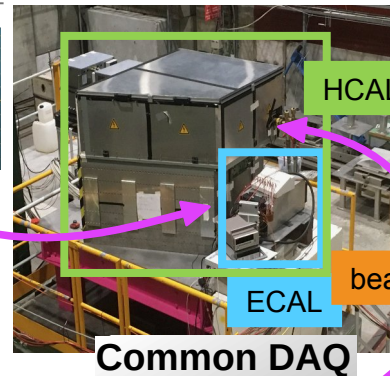
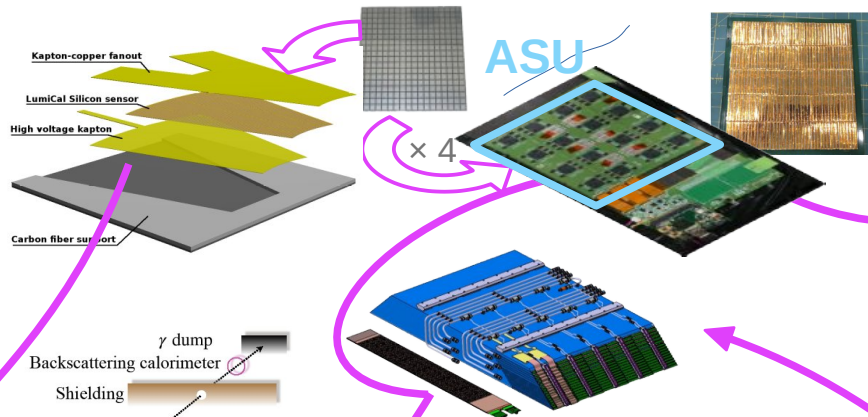


Non-linear QED

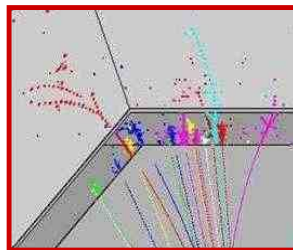
LUXE, SiW-ECAL, ScECAL for ILD

Si 5×5 mm²

Sc 5×50 mm²

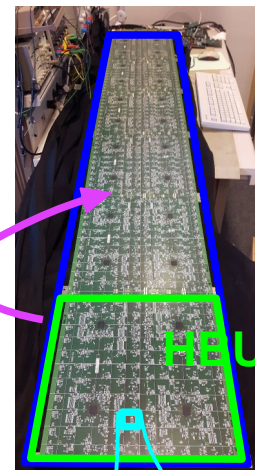


Common DAQ

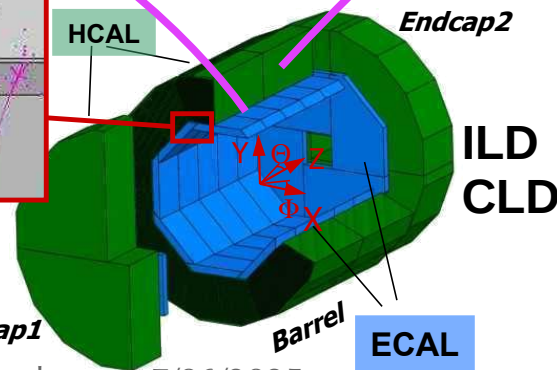


Endcap1

AHCAL for ILD



Scint 3×3 cm²



Endcap2

ILD CLD

Barrel

ECAL

A Map to High-Granularity Calorimeter Prototypes

FCAL for ILD, LUXE

LUXE, SiW-ECAL, ScECAL for ILD

AHCAL for ILD

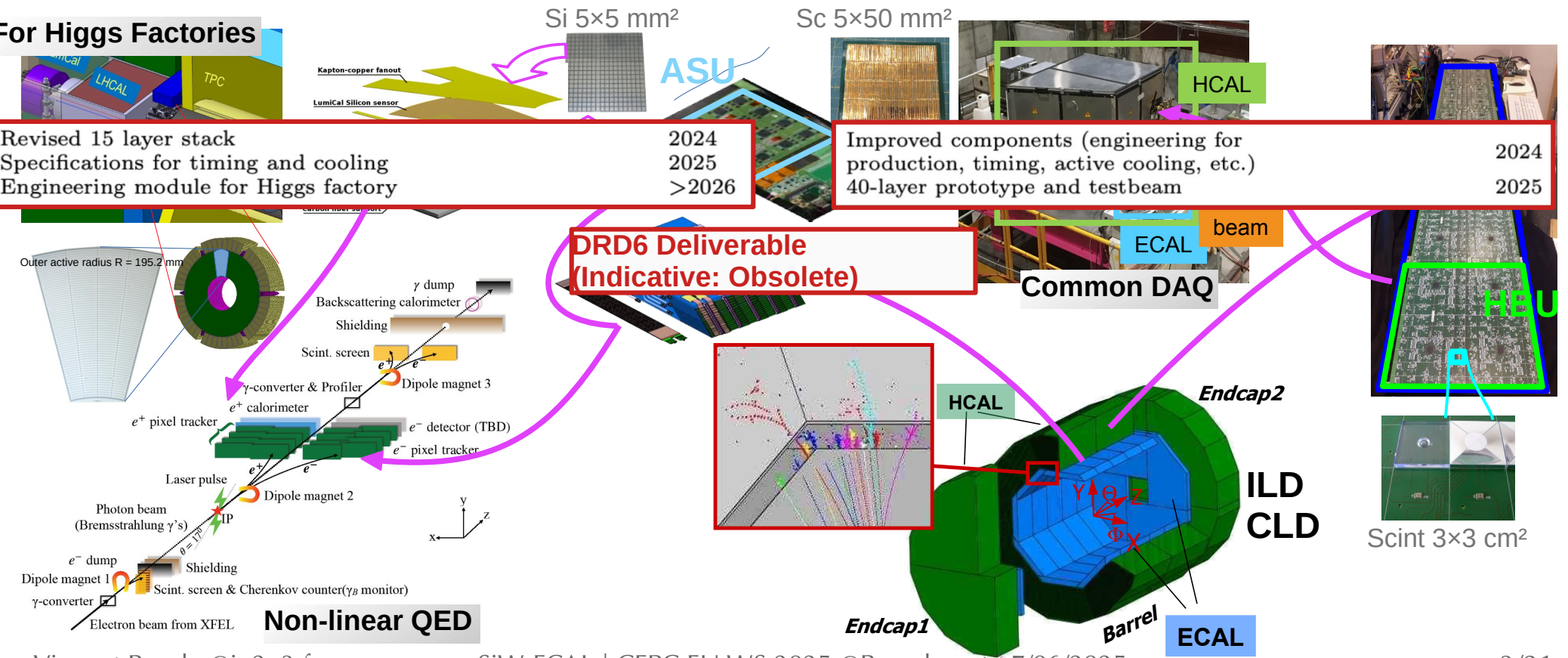
For Higgs Factories

Revised 15 layer stack
Specifications for timing and cooling
Engineering module for Higgs factory

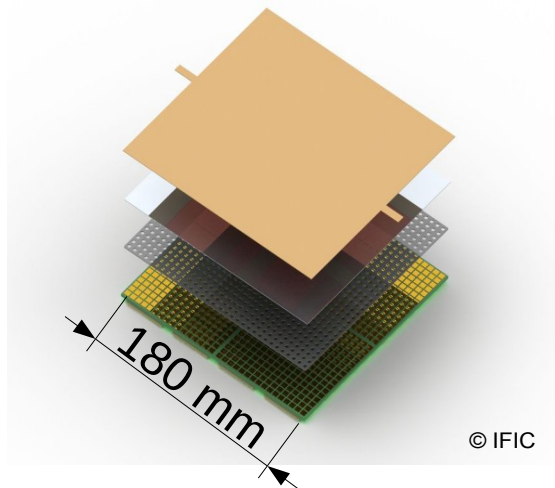
2024
2025
>2026

Improved components (engineering for production, timing, active cooling, etc.)
40-layer prototype and testbeam

2024
2025



SiW-ECAL Active Elements



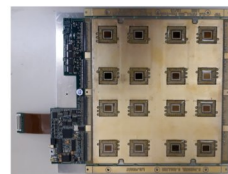
Base element of SiW-ECAL

- Continuous design improvements
 - Noisy-cell fraction ↘
- Delamination issues in 2022
 - New hybridization process needed



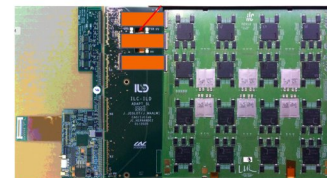
FEV10, 11, 12

- BGA packaging
- Incremental modifications
- From v10 -> v12
- Main “Working horses” since 2014



FEV-COB

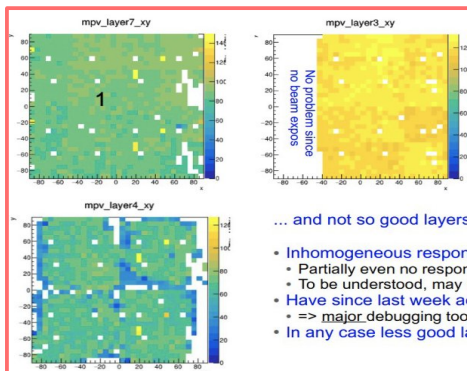
- Chip-On-Board : ASICs wirebonded in cavities
 - Thinner than FEV with BGA
- Based on FEV11
 - External connectivity compatible



FEV13

- BGA packaging
 - Improved routing
 - Local power storage
 - Different external connectivity

2022 DESY & CERN BT



• We have good layers ...

- Homogeneous response to MIPs over layer surface
- Here white cells are masked cells due to PCB routing
 - Understood and will be corrected

... and not so good layers

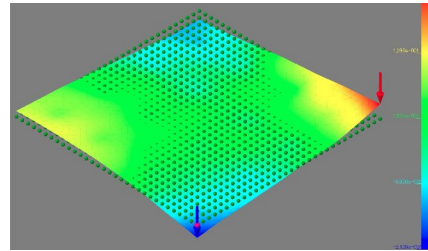
- Inhomogeneous response to MIPs
 - Partially even no response at all, in particular at the wafer boundaries
 - To be understood, may require dedicated aging studies
- Have since last week access to the different stages of the ASICs
 - => major debugging tool
- In any case less good layers will be replaced in coming months

Hybridization studies (2024): How to assemble silicon sensors & PCB ?

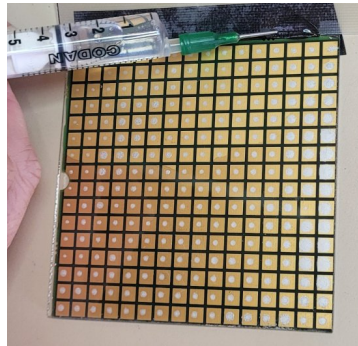
Revisiting gluing (IFIC, IJClab, DMLab)

- PCB metrology
 - Bef. & After curing & soldering
- Glue formula & preparation
- Gluing methods
 - Robot
 - Stencil
- Reenforcement
 - Filling glue
 - Adhesive films

IJClab (méca)

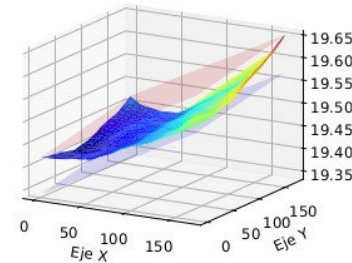


Conductive glue + filling
(~invisible) on a glass plate

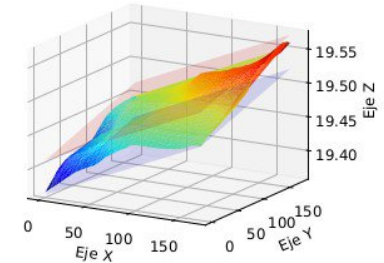


Flatness of PCB

ISOMETRIC VIEW



ISOMETRIC VIEW



Same PCB before / after 10-day dry storage



Measurements by C. Orero, IFIC



Puncturated
adhesive film (**DMLab**)
+
conductive glue dots

Assembly chain:

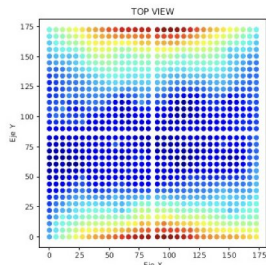
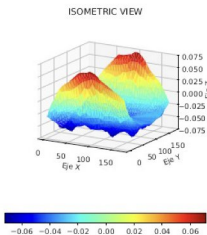
Metrology of PCBs

► We could not do conclusive metrologies of the PCBs upon reception

- Small differences between FEV2.0 and 2.1 and w/ w/o components which make the tools available not suitable... we aim for precision mechanics, we require detailed mechanics models and designs
- At arrival + after drying, requires at least 1 month of time for the full process. → so we decided to dry them before having the definitive tooling (which took some time to be produced)

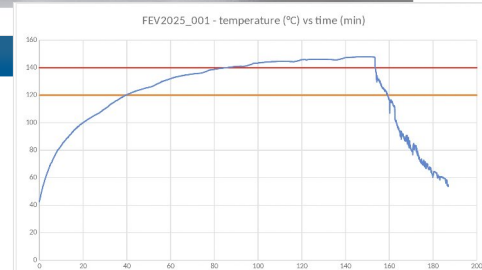
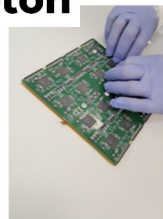
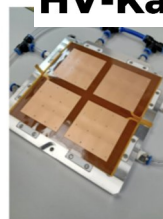
► Metrologies after drying them – FEV2.1 id3 – “flatness” of 145um

File: 20250115_12.53_FEV2.1_id3_JIGALU_optic_AfterSubtraction
Flatness (raw) = 164um
Flatness (optimized) = 145um
Valores rotados: 0.0°



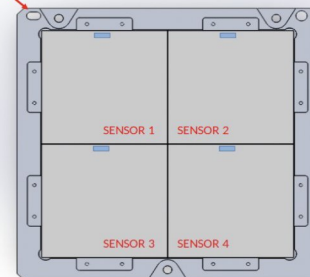
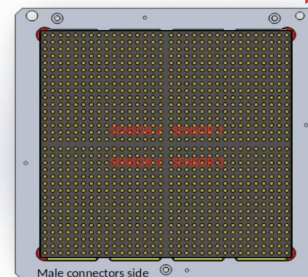
IFIC
INSTITUT DE FÍSICA
CORPUSCULAR

HV-Kapton



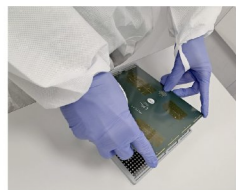
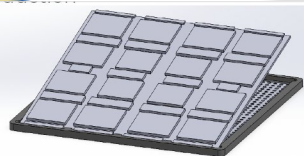
Sensor alignment

Centering pins on top



- PROCEDURE - 3D robot and precifluid v0.odt
- PROCEDURE - CALICE ASU gluing_alignment v0.odt
- PROCEDURE - CALICE ASU gluing v0.odt
- PROCEDURE - H2O preparation v2.odt
- PROCEDURE - HV-Kapton to ASU v0.odt

Sensor and electronics cleaning

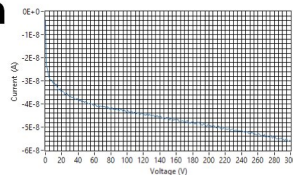
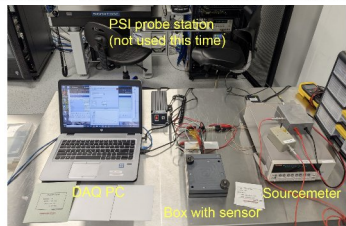


3M tape

Sensor characterization

(Simplified) Setup at IJCLab

Typical I-V Curve



- Reasonable I-V curve though leakage current ~ factor two lower than in HPK data sheet
- Tests allow to validate that there is no major problem with sensors

J. Jeglot, A. Toronto, R.P., (R. Cornat)

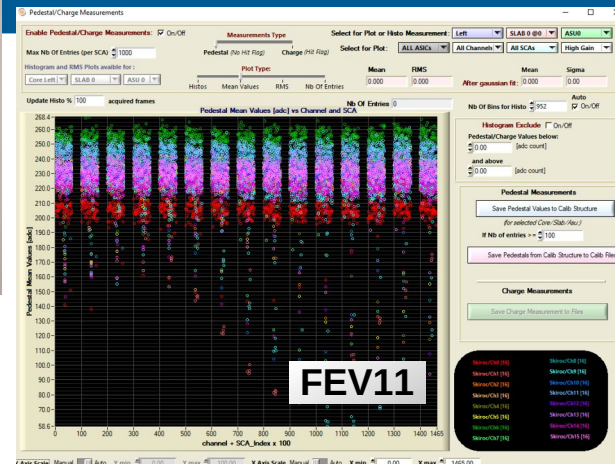
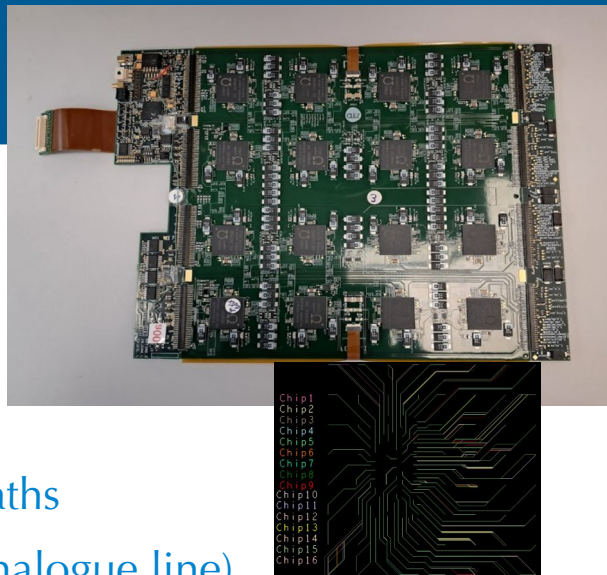
New (ultimate?) FE boards (2023-24)

Improvements:

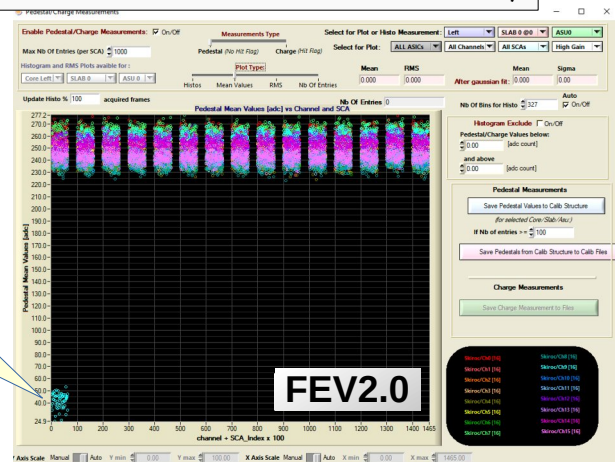
- Power distributions
 - Local LV power regulation: LDO's
 - Local HV filtering & Supply
- Signal distribution (buffering), data paths
- Monitoring (single ID, temp, probe analogue line)
- ASIC shielding/routing

Status:

- Noise uniformity dramatically improved (ex: outliers in thr. / 20)
- version 2.1 produced
 - 4 cabled, 2nd metrology, 2 equipped with sensors (Fev'25)

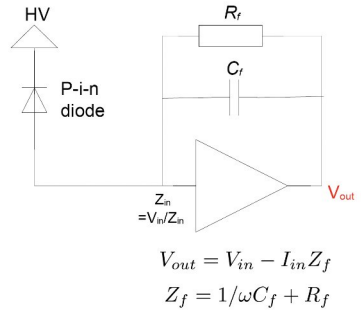
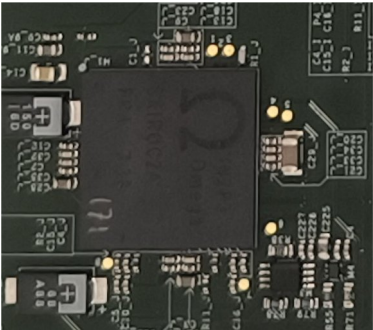


Pedestal measurements vs. Ch# + Mem# x 100)



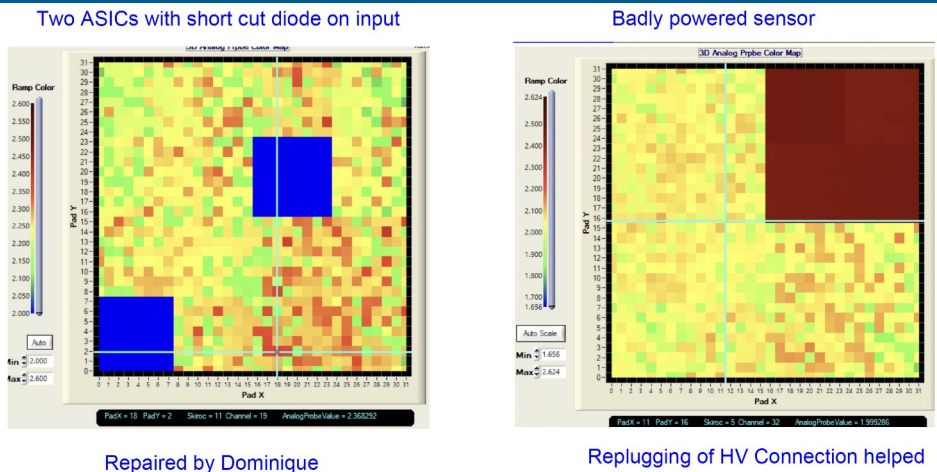
Commissioning: Analogue Probes

Analogue Probes

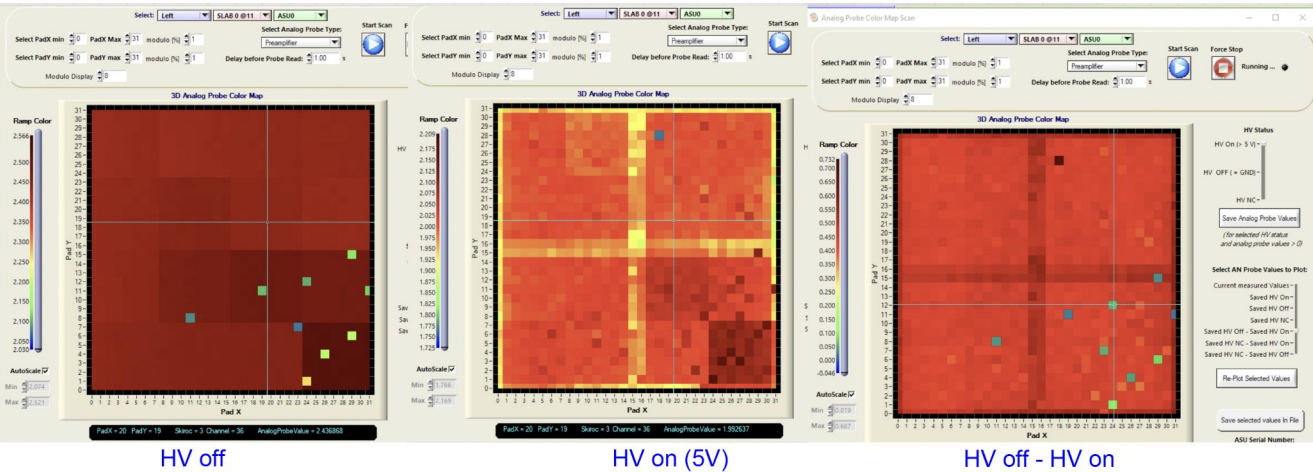


1 value (LV, Channel, ...)
→ common line

Vincent.Boudry@in2p3.fr



- Automatic scan over all 1024 cells (~15 minutes)

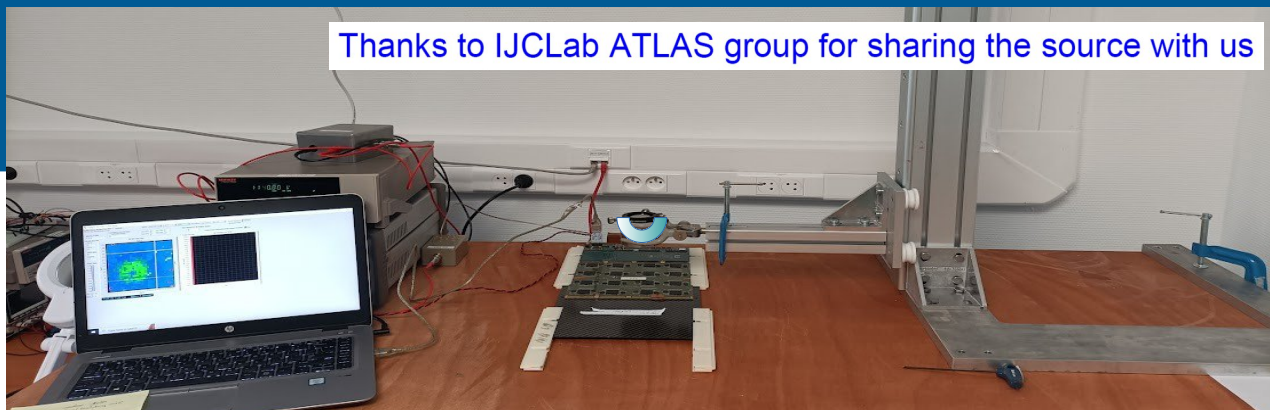


Commissioning: ^{90}Sr

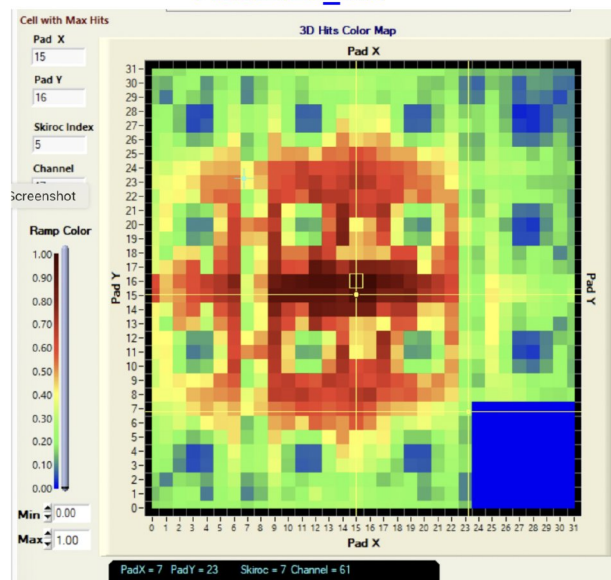
Tests made one week before
BT at DESY

- 1 faulty ASICs AUS01
- Very few noisy channels

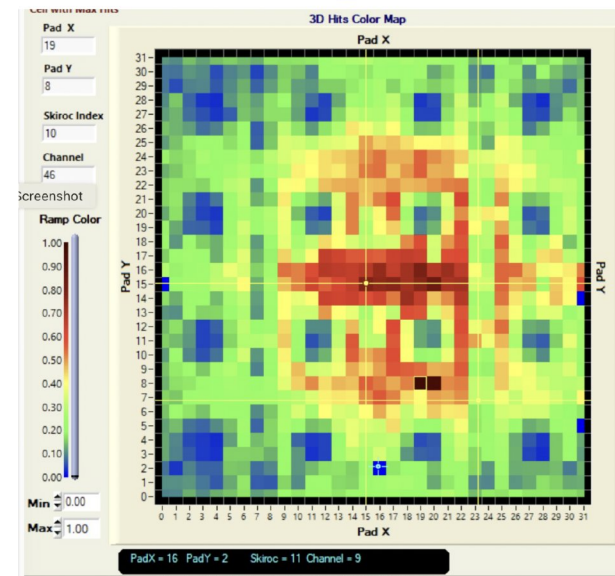
Thanks to IJCLab ATLAS group for sharing the source with us



ASU2025_001



ASU2025_002



- Source tests allow to validate functionality of all cells (or identify further problematic cells)
- Small blue regions ASIC packaging (-> ok), large blue region one faulty chip

DESY Beam Tests 2025/03

1 week 3–10/03/2025

SiW-ECAL:

- 2 new ASU FEv2.1
- 1 ASU COB
- No Tungstens

AHCAL:

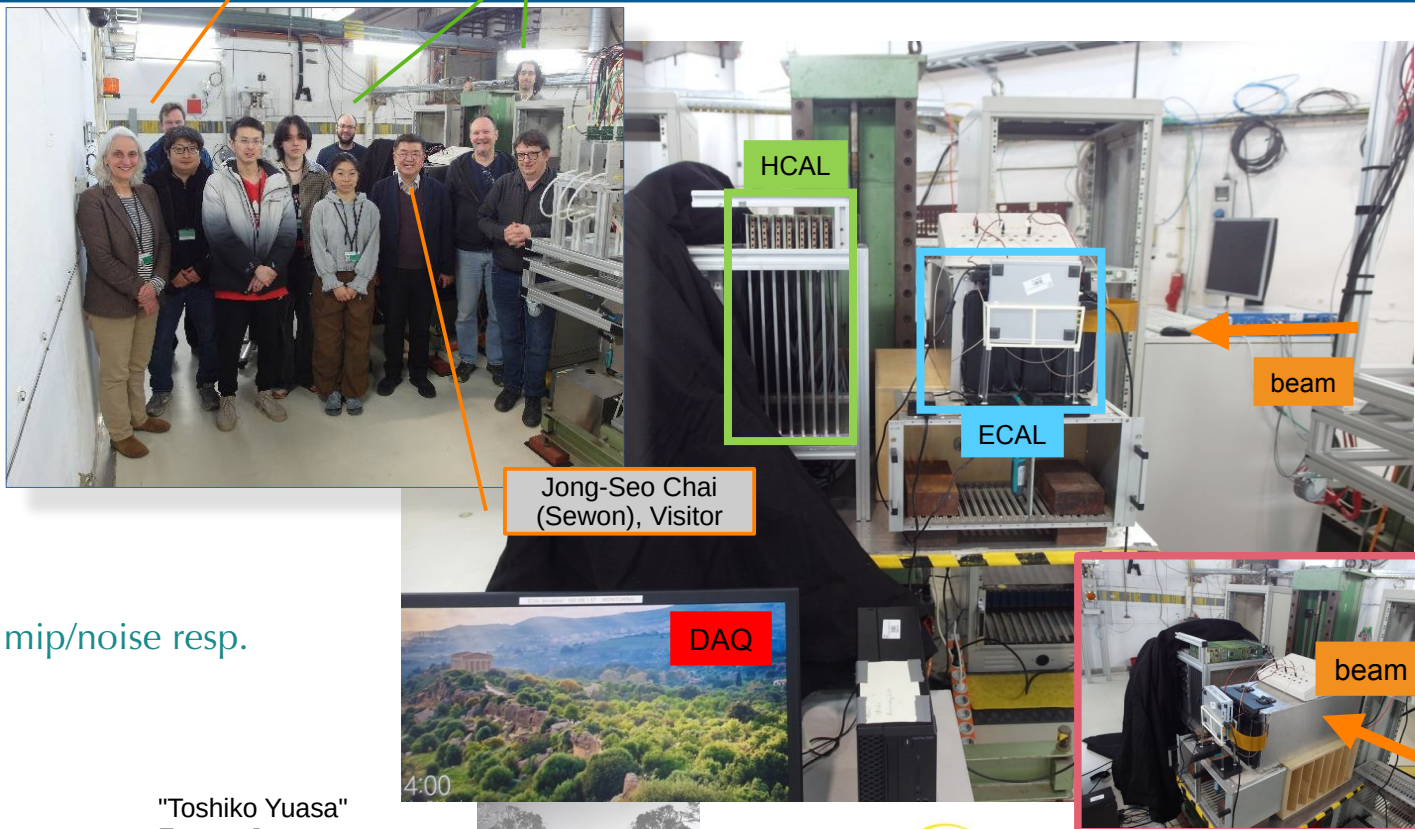
- “Airstack” with 7 short layers

Running:

- 3 days ECAL Stand alone
 - ½ d. install + commissioning
 - Positions scans : uniformity & mip/noise resp.
- 4 days AHCAL
 - ½ d install + repair
 - Scans & TDC runs

Ursula Bassler (LLR / DESY)
Dir Zerwas (DMLab)

Antoine Laudrain (DESY)
Jiri Kvasnicka (FZU)



Jong-Seo Chai
(Sewon), Visitor

DAQ

beam

"Toshiko Yuasa"
France Japan
Particle Physics Network
(TYL-FJPPN)



The measurements leading to these results have been performed at the Test Beam Facility at DESY Hamburg (Germany), a member of the Helmholtz Association (HGF)".

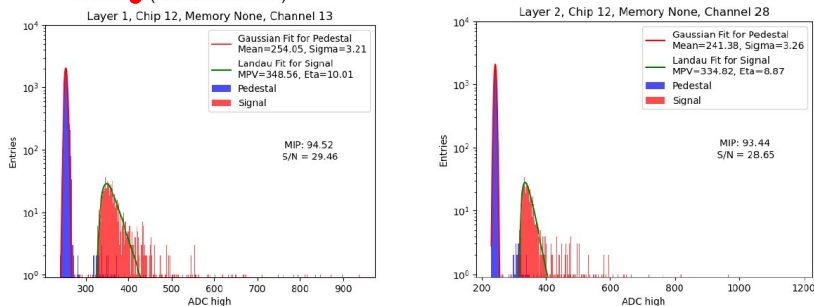
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SiW-ECAL | CEPC EU WS 2025 @Barcelona | 17/06/2025

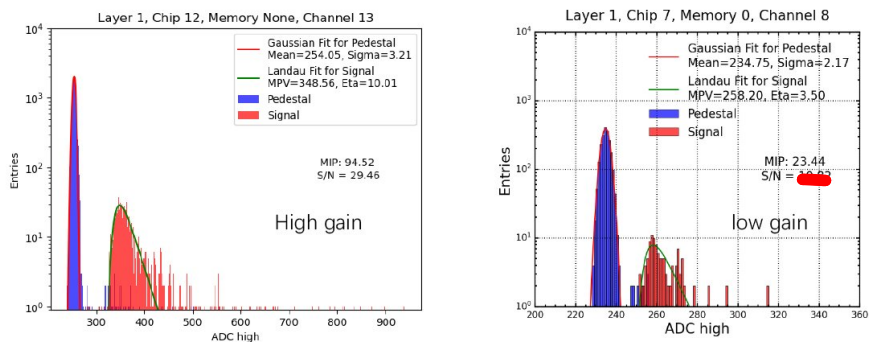
10/21

IJCLab S/N ratio for single channel

- Data: From hold_value scan run (hold value = 130), with high gain of Feedback capacitances
- Pedestal: `adc_high[hitbit_high == 0]`; Signal: `adc_high[hitbit_high == 1]`.
- For ASU1 and ASU2:
 - MIP $\approx$ 93 ADC count
 - S/N $\approx$ 29 (in ADC readout)

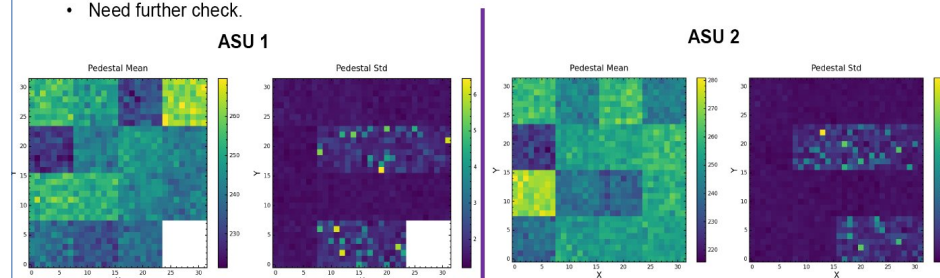


MIP value for different gains of Feedback capacitances



IJCLab Pedestal map of pedestal run

- Data: From pedestal runs
- For each channel:
 - Select `adc_high[hitbit_high == 0 & badbcid == 0]` get the distribution
 - Fit the distribution with gaussian function to get the mean and sigma value
- In each chip, the pedestals are relatively consistent.
- But in some chips, the pedestal sigma is higher than 4 because of two peaks.
- Need further check.



New FEV2.1 preliminary results:

- High S/N ration (MIP MPV/Noise StdDev) $\sim$ 30 in readout branch
- Run in lower gain mode possible
- Very few cells masked

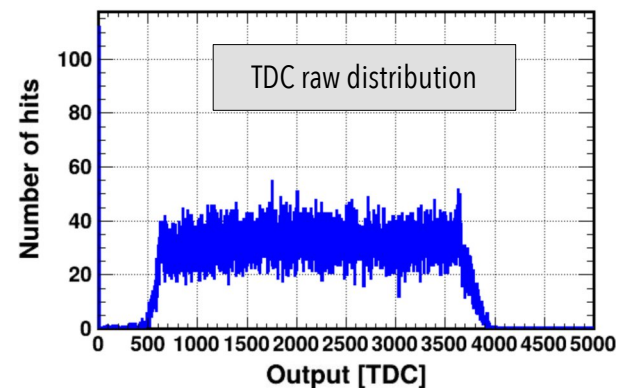
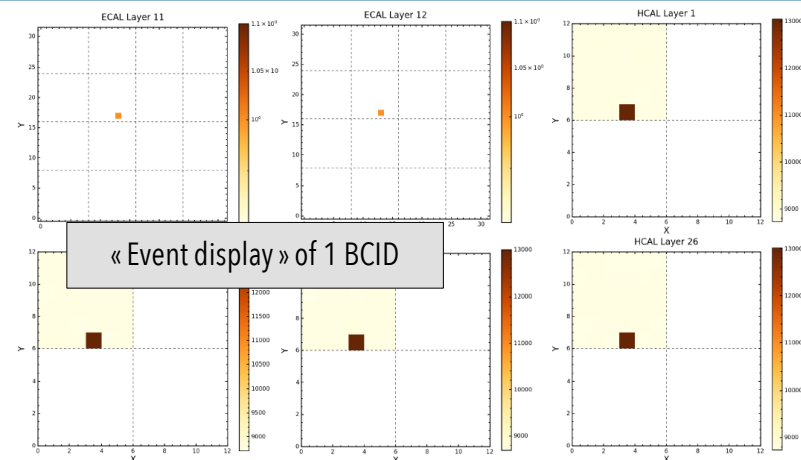
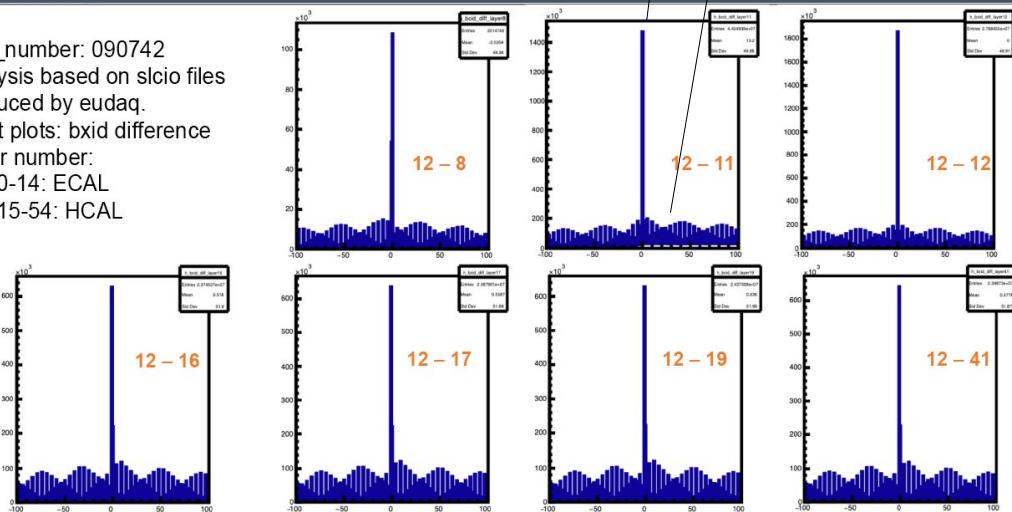
Synchronization ECAL–AHCAL

Aim: consolidate the Digitization, including timing

Set-up identical to 2022

- Same setting as in 2022
 - Bunch Clock cycle offsets (BCID's)
 - Reconstructed Δ BCID's OK
 - TDC information being analysed

- Run_number: 090742
- Analysis based on slcio files produced by eudaq.
- Right plots: bxd difference
- Layer number:
 - 0-14: ECAL
 - 15-54: HCAL



Building of a uniform SiW-ECAL prototype

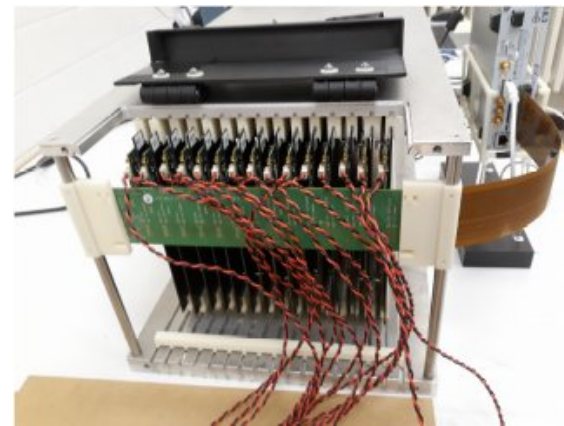
Rationale:

- Current prototype
 - 4(5) types of PCBs $\otimes$ 3 sensor thicknesses (320, 500, 625 μm)
 - (un)gluing issues
- Material for 15 ASUs available $\rightarrow$ full single tower
 - FEV2.1 boards, wafers, components

Application cases :

LUXE@XFEL, EBES@KEK, Lohengrin@ELSA, SHiP?

- Extreme QED & Dark γ searches
 - low energy, rates, ...
 - LUXE: FCAL prototypes $\rightarrow$ common DAQ Application.
 - Could be built from *same cards* in 2×12
 - Needs: sensors (€), (Mech. structure), W
- ⊕ **Will provide operational experience**



Calice TAU sensors for LUXE

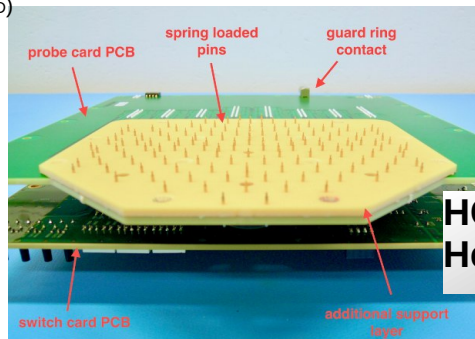
90 CALICE sensors received mid November 2023

A probe card was designed and received in November from CERN

(paid by TAU and IFIC).



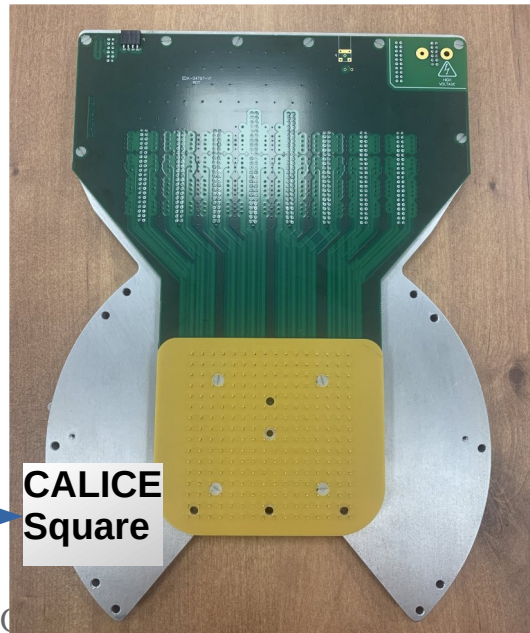
System needed for electrical sensor characterisation in prototyping phase and for quality control in mass production (IV, CV, VBD, VFD, CFD)



HGCAL
Hex



CALICE
Square



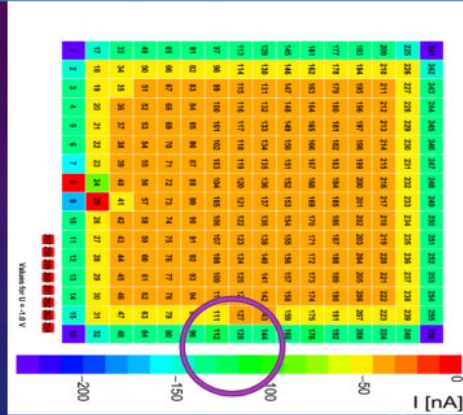
Parameter	Rating	Unit
Device type	P+ PIXEL on N substrate	
Chip size	89700 ± 40 x 89700 ± 40	μ m
Active area	88480 x 88480	μ m
Chip thickness	320 ± 15	μ m
Number of PIXELs	256(16 x 16)	ch
PIXEL pitch	5530 x 5530	μ m
PIXEL GAP	10	μ m

Parameter	Symbol	Condition	Min	Typ	Max	Unit
substrate resistence			3	---	---	kΩ · cm
Full depletion voltage	Vfd		15	---	120	V
leakage current(for inner PIXEL*2)	Id	VR=200V	---	---	25	nA
leakage current(for outer PIXEL*2)	Id2	VR=200V	---	---	100	nA
Number of NG PIXEL			---	---	10	ch

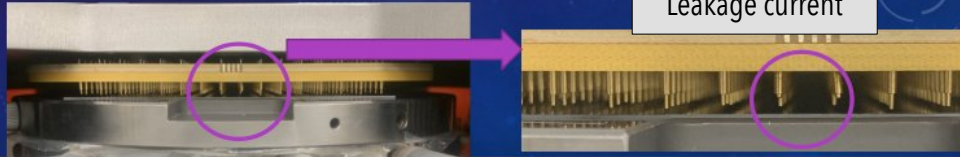
Test procedures

DATA TAKING

- 1st step : contact test to be sure all the pads are touching the probe pins. Takes few minutes
- 2nd step IV test.
- 3rd step CV test.
- We are adding the following steps :
 - Rotation of the sensors (90 degrees)
 - Contact test
 - IV and CV for the missing pins



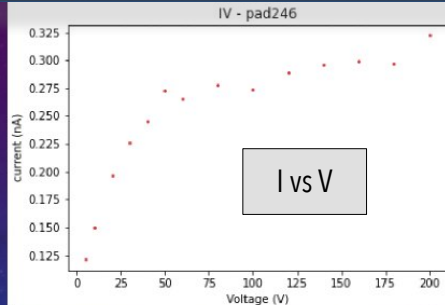
Leakage current



IV MEASUREMENT

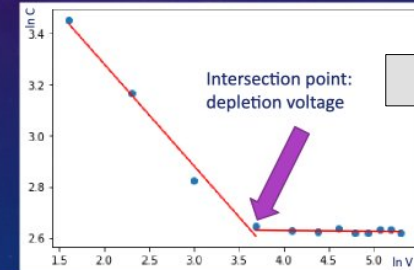
Checked the influence of different parameters:
delay between measurements, delay between
voltage change,...

System tuned



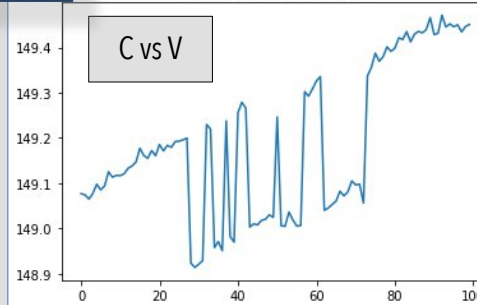
DEPLETION VOLTAGE

- It is possible to extract the depletion voltage from the CV measurement; the capacitance can be modeled by:
- $$C_g = A \frac{\epsilon_{Si} \epsilon_0}{w} = \begin{cases} A \sqrt{\frac{\epsilon_{Si} \epsilon_0 e N_d}{2V}} & \text{for } V < V_d, A: \text{pad area } N_d: \text{number of donor, } V: \text{bias voltage} \\ A \frac{\epsilon_{Si} \epsilon_0}{w_m} & \text{for } V > V_d, w_m: \text{max. depletion width} \end{cases}$$
- So if we take the log of C_g , we should obtain two lines. The intersection of these lines is giving the depletion voltage

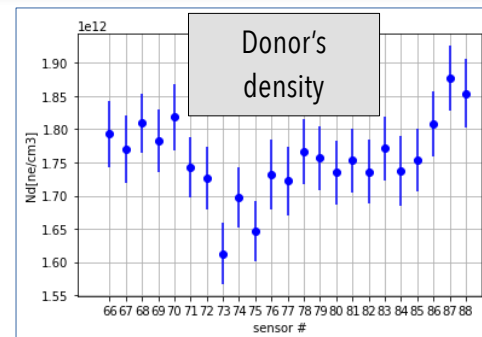


CV measurement pad 55

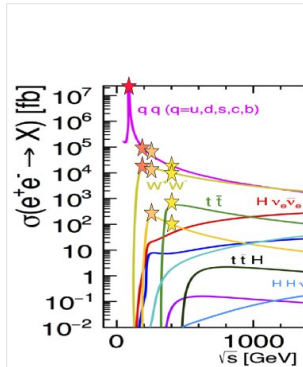
C vs V



Donor's density



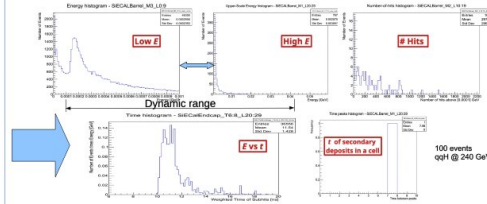
Fluxes in Calorimeters



Processes: min. bias

- All
 - $ee \rightarrow qq$
 - $Ee \rightarrow \mu\mu, \tau\tau$
 - $ee \rightarrow ee$ ($\gg$ Bhabha)
 - $\gamma\gamma \rightarrow VV$
 - Machine background (ee pairs)
- $E_{CM} \geq 160$ GeV
 - $ee \rightarrow WW$
- $(E_{CM} \geq 240$ GeV)
 - $ee \rightarrow HZ$
- $(E_{CM} \geq 360$ GeV)
 - $ee \rightarrow tt$

Full simulation ILD $\rightarrow$ statistics per region



$\times \mathcal{L} +$ Machine background

$\rightarrow$ Fluxes of hits, data, per region

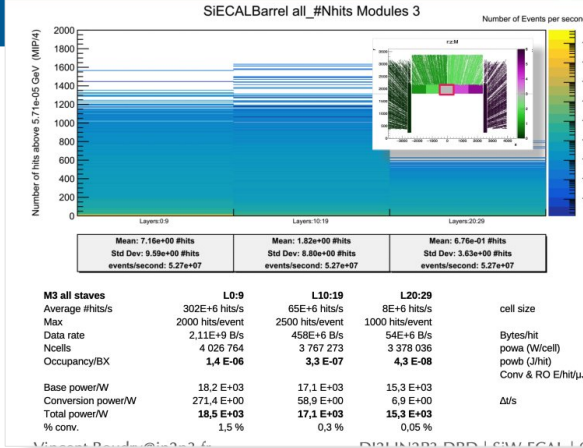
$\rightarrow$ Power with ASIC assumptions

Take Home:

- Even at Z peak power dominated by pre-amp ($\leftrightarrow$ conversion power in negligible)
- Tool is there, missing:
 - Digitization (easier way in Key4HEP ?)
 - Mapping needs to be adapted for each calorimeter readout topology

Results : Rates in Silicon ECAL Barrel, Central Module vs depth

Similar results for ScECAL, SDHCAL, AHCAL



Distributions of the number of hits crossing (MIP/4) energy threshold of all the physics processes and machine background at 91.2 GeV (FCC-Z4)
The z scale is the number of event/s

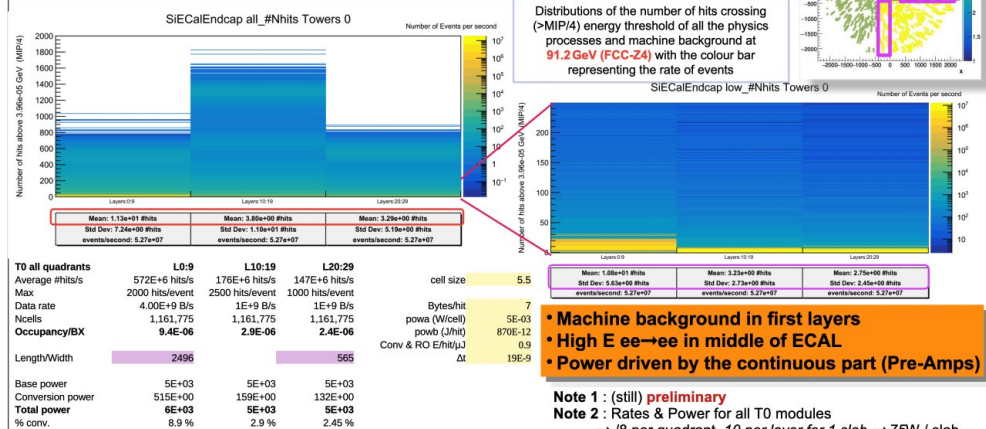
- From the $\langle f_{\text{hits}} \rangle$ in one region one can extract :
- The data rate, knowing the number of bytes per hits (here 7 as a landmark)
 - The occupancy, knowing the number of cell in the region.
 - The power dissipated on elec. power (here for SKIROC2 like chip)

- Most of the hits are in the first third of the calorimeter.
- Highest average rates L0:9
- Highest max rates in L10:19

Note 1 : (still) preliminary
Note 2 : Rates & Power for all M3 modules
 $\rightarrow$ 8 per module, 10 per layer for 1 slab
 $\rightarrow$ 50 W/slab

Results: Rates in SiECAL EndCaps, Tower 0 vs depth

Similar results for ScECAL, SDHCAL, AHCAL



Distributions of the number of hits crossing ($>$ MIP/4) energy threshold of all the physics processes and machine background at 91.2 GeV (FCC-Z4) with the colour bar representing the rate of events

- Machine background in first layers
- High $E_{ee} \rightarrow ee$ in middle of ECAL
- Power driven by the continuous part (Pre-Amps)

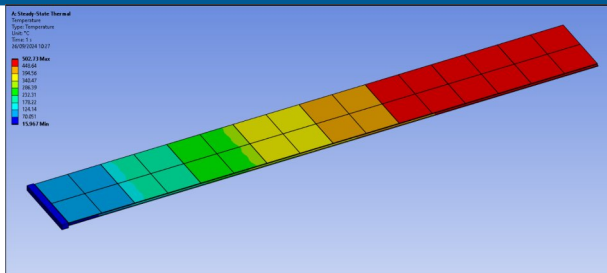
Note 1 : (still) preliminary
Note 2 : Rates & Power for all T0 modules
 $\rightarrow$ 8 per quadrant, 10 per layer for 1 slab $\rightarrow$ 75W / slab

ECAL adaptation : flat cold plate, preliminary thermal studies

Uniform solutions:

“Standard Slab”:

- 8 ASU (1440mm)_z, 8192 ch / 128 ASICs
- 100 W



Passive cooling: Cu of 2mm (W, C ignored)

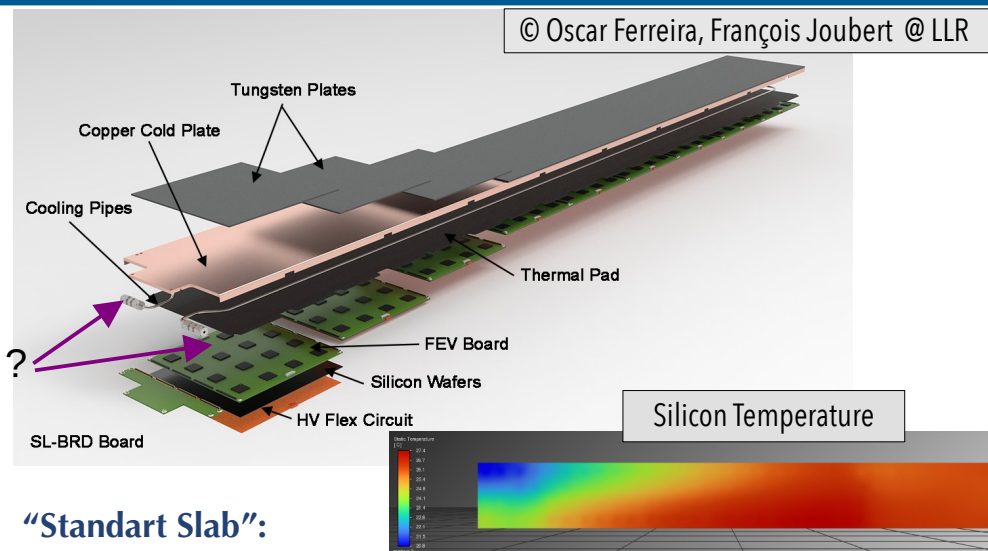
Adiabatic, but for heat bridge at the end

$\Delta T = 500^{\circ}\text{C}$ on Wafer surface at $t = \infty$

Status:

- Limited flow of water seems enough...
- Now looking into pipe in 4-mm Cu layer
 - Replaces ~1 mm of W
- To be validated on simulations

Connections ?



“Standard Slab”:

- 8 ASU (1440mm), 8192 ch / 128 ASICs
- 128 W (1W/ASIC ~16 mW /ch)

Active cooling:

- 4 mm Cu plate with 1/8" Stainless Steel Tubing
- 0.2 ℓ/min of water @ 15°C

Adiabatic, but for heat bridge at the end

$\Delta T = 6.6^{\circ}\text{C}$ on Wafer surface at $t = \infty$

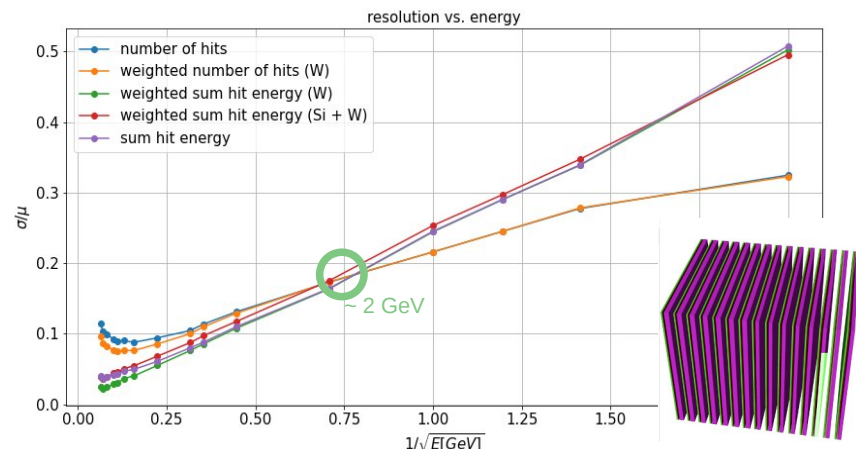
Re-optimization of the design required (on-going)

Energy reconstruction methods

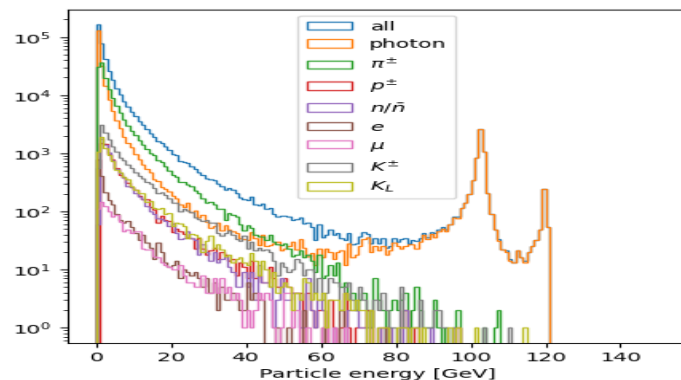
- Counting (Digital) vs Analog
 - Better by counting for $E_\gamma < \sim 2$ GeV
 - How to best combine them ?
 - New methods ?
- π^0 reconstruction from improved positions
- Timing with 50 ps ? $\Leftarrow$ 3 years programme started.

Re-optimization of sampling :

- Part of W $\rightarrow$ 4 mm of copper for cooling
- Optimisation for counting at low-E / Start of showers
Lower the detection threshold (≤ 100 MeV ?)
- Work done for LUXE as a method
(Zarnecki et al, arXiv:2409.19654v1)



SiW-ECAL Prototype of 2022 (15 layers) [Yukun Shi]



Jet Composition at 91 GeV (Hao Liang)

Recent Progress: CALOROC1C design (Si and ℓ Ar) – Ω mega

New ASICs

- Based on HGCROC, HKROC

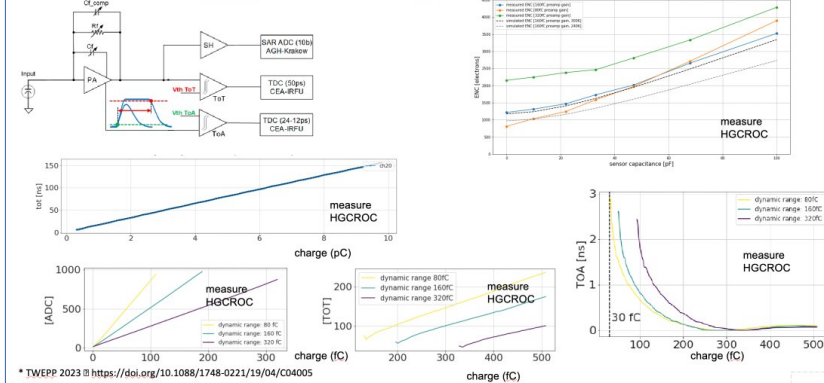
Compatibility:

- PCB & DAQ work can start with HKROC

Vincent.Boudry@in2p3.fr

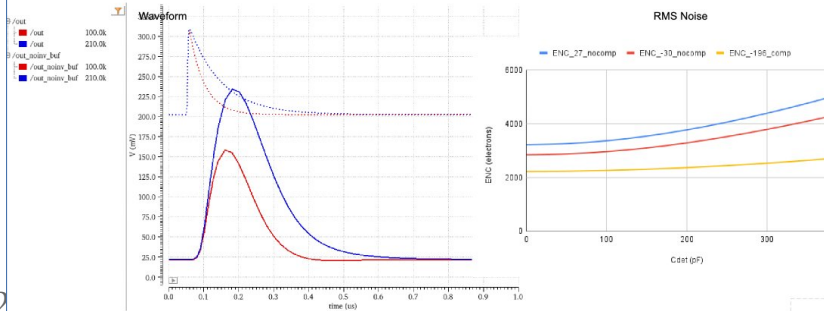
CALOROC1C (based on HGCROC)

- Reuse of analog front-end based on ADC/TOT and TOA: fully characterized *
 - 15 mW per channel / Radiation performance / Si up to 100 pF



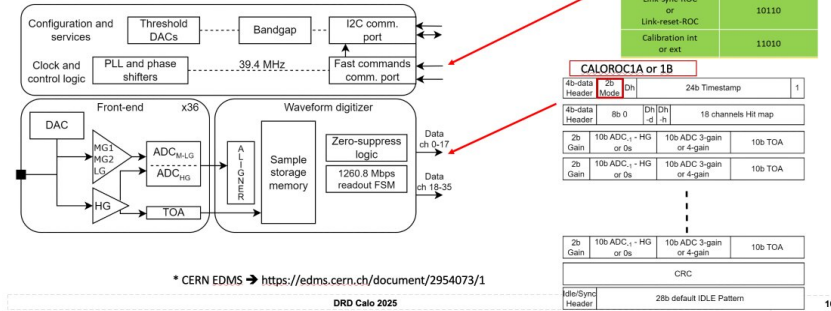
CALOROC1C (based on HGCROC)

- CALOROC1C will
 - update its back-end (readout streaming)
 - slow down the shaping from 25ns to 100ns



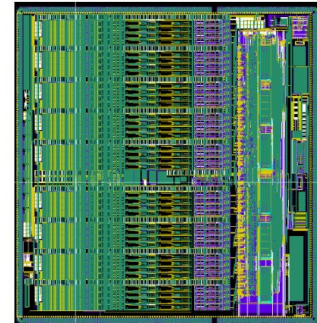
CALOROCs: block diagram and interfaces

- CALOROCs will have the same interfaces (comparable to CMS H2GCROC *):
 - Fast command to dynamically control the ASIC
 - I2C to set the parameters
 - High speed serial links (CernLowPowerSignal compatible)



Conclusion

- Conservative **CALOROC1A**:
 - Based on CMS SiPM H2GCROC + SRO
- New **CALOROC1B**:
 - New analog front end
 - Higher dynamic range and input capacitance
 - Same backend (and pinout)
- CALOROC1C** for Si/LAr detectors:
 - Based on CMS Si HGCROC + SEO
- All Calorocs share the same backend
- All Calorocs will be sent to fabrication this month



CALOROCs are targeted to include all features + radiation hardness on the first submission



Conclusions

SiW-ECAL

- 2 new board produced and put in beam for low-E response
- Preliminary results very promising: OK for production of + 13 new ones
- Will provide input for Digitization code adjustment

SiW-ECAL Future test:

- **2026**, with full uniform stack of 15 layers, then a long slab
 - Will be used for small experiments (EBES, LUXE, Lohengrin) → operational experience
 - Design will serve a basis for future μ -Electronics

Coming developments:

- Thin Cold-Plate prototyping + Interfaces (SiW-ECAL)
 - Re-optimisation of **absorbers** + **timing** + **`digital modes`**
- Re-design the PCBs on the basis of new ASICs
 - I2C communication (HGCALE protocols)
- Re-design of DAQ
 - Rates estimations on-going in all calorimeters
- Should aim at scalable prototypes by early 2030's
 - Reminder: 8 years of building for large calos

Possible planning (FCC-ee)

